

# Shizuo Fujita

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

137  
papers

5,301  
citations

36  
h-index

70  
g-index

142  
ext. papers

5,875  
ext. citations

2  
avg. IF

5.93  
L-index

#	Paper	IF	Citations
137	Novel p-type oxides with corundum structure for gallium oxide electronics. <i>Journal of Materials Research</i> , <b>2022</b> , 37, 651-659	2.5	2
136	Prospects for phase engineering of semi-stable Ga <sub>2</sub> O <sub>3</sub> semiconductor thin films using mist chemical vapor deposition. <i>Journal of Applied Physics</i> , <b>2022</b> , 131, 090902	2.5	8
135	Research of Semiconductor Materials That Emit in the Vacuum Ultraviolet Region of 200 nm or Less. <i>Zairyo/Journal of the Society of Materials Science, Japan</i> , <b>2021</b> , 70, 727-731	0.1	
134	Ultra-wide bandgap corundum-structured p-type $\text{H}(\text{Ir,Ga})\text{O}_3$ alloys for $\text{HGa}_2\text{O}_3$ electronics. <i>Applied Physics Letters</i> , <b>2021</b> , 118, 102104	3.4	14
133	Analysis of Deep Traps in Mist Chemical Vapor Deposition-Grown n-Type $\text{HGa}_2\text{O}_3$ by Photocapacitance Method. <i>Physica Status Solidi (B): Basic Research</i> , <b>2021</b> , 258, 2000622	1.3	3
132	Thermal stability of $\text{H}(\text{Al}_x\text{Ga}_{1-x})\text{O}_3$ films grown on c-plane sapphire substrates with an Al composition up to 90%. <i>Japanese Journal of Applied Physics</i> , <b>2021</b> , 60, SBBD13	1.4	6
131	Identification of free and bound exciton emission of MgO single crystal in vacuum ultraviolet spectral range. <i>Applied Physics Letters</i> , <b>2021</b> , 119, 132105	3.4	1
130	Impact of hydrochloric acid on the epitaxial growth of In <sub>2</sub> O <sub>3</sub> films on (0001) $\text{HAl}_2\text{O}_3$ substrates by mist CVD. <i>Applied Physics Express</i> , <b>2020</b> , 13, 075504	2.4	3
129	Thermal stability of $\text{HGa}_2\text{O}_3$ films grown on c-plane sapphire substrates via mist-CVD. <i>AIP Advances</i> , <b>2020</b> , 10, 115013	1.5	8
128	Pure deep-ultraviolet cathodoluminescence from rocksalt-structured MgZnO grown with carbon-free precursors. <i>Applied Physics Express</i> , <b>2019</b> , 12, 052011	2.4	10
127	Enhancement of epitaxial lateral overgrowth in the mist chemical vapor deposition of $\text{HGa}_2\text{O}_3$ by using a-plane sapphire substrate. <i>Japanese Journal of Applied Physics</i> , <b>2019</b> , 58, 120912	1.4	16
126	A power device material of corundum-structured $\text{HGa}_2\text{O}_3$ fabricated by MIST EPITAXY technique. <i>Japanese Journal of Applied Physics</i> , <b>2018</b> , 57, 02CB18	1.4	50
125	Electrical characterization of Si-doped n-type $\text{HGa}_2\text{O}_3$ on sapphire substrates. <i>MRS Advances</i> , <b>2018</b> , 3, 171-177	0.7	24
124	Control of Crystal Structure of Ga <sub>2</sub> O <sub>3</sub> on Sapphire Substrate by Introduction of $\text{H}(\text{Al}_x\text{Ga}_{1-x})\text{O}_3$ Buffer Layer. <i>Physica Status Solidi (B): Basic Research</i> , <b>2018</b> , 255, 1700326	1.3	27
123	Evaluation of band alignment of $\text{HGa}_2\text{O}_3/\text{H}(\text{Al}_x\text{Ga}_{1-x})\text{O}_3$ heterostructures by X-ray photoelectron spectroscopy. <i>Japanese Journal of Applied Physics</i> , <b>2018</b> , 57, 040314	1.4	29
122	Deep-Ultraviolet Luminescence of Rocksalt-Structured $\text{Mg}_x\text{Zn}_{1-x}\text{O}$ ( $x > 0.5$ ) Films on MgO Substrates. <i>Journal of Electronic Materials</i> , <b>2018</b> , 47, 4356-4360	1.9	10
121	Electrical properties of $\text{Hr}_2\text{O}_3/\text{HGa}_2\text{O}_3$ pn heterojunction diode and band alignment of the heterostructure. <i>Applied Physics Letters</i> , <b>2018</b> , 113, 212104	3.4	49

120	Tin oxide coating by nonvacuum-based mist chemical vapor deposition on stainless steel separators for polymer electrolyte fuel cells. <i>Japanese Journal of Applied Physics</i> , <b>2018</b> , 57, 117103	1.4	20
119	Corundum-Structured $\text{In}_2\text{O}_3$ as a Wide-Bandgap Semiconductor for Electrical Devices. <i>MRS Advances</i> , <b>2017</b> , 2, 301-307	0.7	5
118	Corundum-structured $\text{InGa}_2\text{O}_3$ -based alloys for future power device applications <b>2017</b> ,		1
117	Conductivity control of Sn-doped $\text{InGa}_2\text{O}_3$ thin films grown on sapphire substrates. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 1202BA	1.4	63
116	Growth of rocksalt-structured $\text{Mg}_x\text{Zn}_{1-x}\text{O}$ ( $x > 0.5$ ) films on MgO substrates and their deep-ultraviolet luminescence. <i>Applied Physics Express</i> , <b>2016</b> , 9, 111102	2.4	15
115	Reduction in edge dislocation density in corundum-structured $\text{InGa}_2\text{O}_3$ layers on sapphire substrates with quasi-graded $\text{AlGa}_2\text{O}_3$ buffer layers. <i>Applied Physics Express</i> , <b>2016</b> , 9, 071101	2.4	49
114	Growth characteristics of corundum-structured $\text{AlGaIn}_2\text{O}_3/\text{Ga}_2\text{O}_3$ heterostructures on sapphire substrates. <i>Journal of Crystal Growth</i> , <b>2016</b> , 436, 150-154	1.6	50
113	Crystal Growth and Device Applications of Corundum-Structured Gallium Oxide. <i>Zairyo/Journal of the Society of Materials Science, Japan</i> , <b>2016</b> , 65, 631-637	0.1	
112	Silver oxide Schottky contacts and metal semiconductor field-effect transistors on $\text{SnO}_2$ thin films. <i>Applied Physics Express</i> , <b>2016</b> , 9, 041101	2.4	21
111	Characterization of band offset in $\text{Al}_x\text{Ga}_{1-x}\text{O}_3/\text{InGa}_2\text{O}_3$ heterostructures <b>2016</b> ,		1
110	Surface termination structure of $\text{InGa}_2\text{O}_3$ film grown by mist chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2016</b> , 108, 251602	3.4	20
109	Evolution of corundum-structured III-oxide semiconductors: Growth, properties, and devices. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 1202A3	1.4	81
108	Homoepitaxial growth of beta gallium oxide films by mist chemical vapor deposition. <i>Japanese Journal of Applied Physics</i> , <b>2016</b> , 55, 1202B8	1.4	51
107	Transparent conductive zinc-oxide-based films grown at low temperature by mist chemical vapor deposition. <i>Thin Solid Films</i> , <b>2015</b> , 597, 30-38	2.2	37
106	Vertical Schottky barrier diodes of $\text{InGa}_2\text{O}_3$ fabricated by mist epitaxy <b>2015</b> ,		3
105	Growth and metal-oxide-semiconductor field-effect transistors of corundum-structured alpha indium oxide semiconductors. <i>Applied Physics Express</i> , <b>2015</b> , 8, 095503	2.4	14
104	Enhanced thermal stability of alpha gallium oxide films supported by aluminum doping. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 030301	1.4	33
103	Wide-bandgap semiconductor materials: For their full bloom. <i>Japanese Journal of Applied Physics</i> , <b>2015</b> , 54, 030101	1.4	201

102	Mist chemical vapor deposition of aluminum oxide thin films for rear surface passivation of crystalline silicon solar cells. <i>Applied Physics Express</i> , <b>2014</b> , 7, 021303	2.4	15
101	Ultrasonic-assisted mist chemical vapor deposition of II-oxide and related oxide compounds. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2014</b> , 11, 1225-1228		19
100	Growth of corundum-structured $(\text{In}_x\text{Ga}_{1-x})_2\text{O}_3$ alloy thin films on sapphire substrates with buffer layers. <i>Journal of Crystal Growth</i> , <b>2014</b> , 401, 670-672	1.6	30
99	Aluminum Oxide Passivation Layer for Crystalline Silicon Solar Cells Deposited by Mist CVD in Open-Air Atmosphere. <i>Materials Research Society Symposia Proceedings</i> , <b>2014</b> , 1647, 1		
98	Epitaxial growth of corundum-structured wide band gap III-oxide semiconductor thin films. <i>Journal of Crystal Growth</i> , <b>2014</b> , 401, 588-592	1.6	102
97	Band gap and function engineering for novel functional alloy semiconductors: Bloomed as magnetic properties at room temperature with $\text{Fe}(\text{GaFe})_2\text{O}_3$ . <i>Journal of Applied Physics</i> , <b>2013</b> , 113, 233907-5	1.5	53
96	Growth of corundum-structured $\text{In}_2\text{O}_3$ thin films on sapphire substrates with $\text{Fe}_2\text{O}_3$ buffer layers. <i>Journal of Crystal Growth</i> , <b>2013</b> , 364, 30-33	1.6	55
95	Formation of Semi-Insulating Layers on Semiconducting $\text{FeGa}_2\text{O}_3$ Single Crystals by Thermal Oxidation. <i>Japanese Journal of Applied Physics</i> , <b>2013</b> , 52, 051101	1.4	25
94	Thermal stability of single crystalline alpha gallium oxide films on sapphire substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2013</b> , 10, 1592-1595		47
93	Fabrication of Corundum-Structured $\text{Fe}(\text{InFe})_2\text{O}_3$ Alloy Films on Sapphire Substrates by Inserting $\text{Fe}_2\text{O}_3$ Buffer Layer. <i>Materials Research Society Symposia Proceedings</i> , <b>2013</b> , 1494, 221-225		1
92	Crystal Structure of Non-Doped and Sn-Doped $\text{Fe}(\text{GaFe})_2\text{O}_3$ Thin Films.. <i>Materials Research Society Symposia Proceedings</i> , <b>2013</b> , 1494, 147-152		3
91	Oriented growth of beta gallium oxide thin films on yttrium-stabilized zirconia substrates. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2013</b> , 10, 1596-1599		17
90	Formation of aluminum tris (8-hydroxyquinoline) solution in methanol and fabrication of thin films by ultrasonic spray-assisted vapor deposition. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2012</b> , 209, 1298-1301	1.6	8
89	Thin Film Formation of Transparent Conductive Oxides by Solution-Based Mist Deposition Method toward Hybrid Device Applications. <i>Materials Research Society Symposia Proceedings</i> , <b>2012</b> , 1400, 1		2
88	Fabrication of Organic Polymer Solar Cells by a Novel Solution-Based Vapor-like Mist Deposition Method. <i>Materials Research Society Symposia Proceedings</i> , <b>2012</b> , 1390, 47		2
87	Fabrication of Organic Small Molecular Thin Films based on Ultrasonic Spray-Assisted Vapor-Deposition Method. <i>Materials Research Society Symposia Proceedings</i> , <b>2012</b> , 1400, 29		
86	Growth and Band Gap Control of Corundum-Structured $\alpha\text{-(AlGa)}_2\text{O}_3$ Thin Films on Sapphire by Spray-Assisted Mist Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 100207	1.4	30
85	Evaluation of Misfit Relaxation in $\text{FeGa}_2\text{O}_3$ Epitaxial Growth on $\text{FeAl}_2\text{O}_3$ Substrate. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 020201	1.4	15

84	Electrical Conductive Corundum-Structured $\beta$ -Ga <sub>2</sub> O <sub>3</sub> Thin Films on Sapphire with Tin-Doping Grown by Spray-Assisted Mist Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2012</b> , 51, 070203	1.4	15
83	Fundamental Properties and Optical Device Applications of ZnO. <i>The Review of Laser Engineering</i> , <b>2011</b> , 39, 165-170	0	
82	Extraction of Trap Densities in ZnO Thin-Film Transistors and Dependence on Oxygen Partial Pressure During Sputtering of ZnO Films. <i>IEEE Transactions on Electron Devices</i> , <b>2011</b> , 58, 3018-3024	2.9	20
81	Fabrication of PEDOT:PSS/ZnMgO Schottky-type ultraviolet sensors on glass substrates with solution-based mist deposition technique and hard-mask patterning. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 613-615		21
80	Growth of SnO <sub>2</sub> crystalline thin films by mist chemical vapour deposition method. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2011</b> , 8, 540-542		35
79	Reduction of Photo-Leakage Current in ZnO Thin-Film Transistors With Dual-Gate Structure. <i>IEEE Electron Device Letters</i> , <b>2011</b> , 32, 509-511	4.4	6
78	Effects of chemical stoichiometry of channel region on bias instability in ZnO thin-film transistors. <i>Applied Physics Letters</i> , <b>2011</b> , 98, 103512	3.4	12
77	Ultrasonic Spray-Assisted Solution-Based Vapor-Deposition of Aluminum Tris(8-hydroxyquinoline) Thin Films. <i>Japanese Journal of Applied Physics</i> , <b>2011</b> , 50, 020204	1.4	4
76	Artificial Surface Control of Gallium Oxide Semiconductors and Growth of High Quality Single-crystalline Thin Films. <i>Hyomen Kagaku</i> , <b>2010</b> , 31, 643-650		
75	Mechanism analysis of photoleakage current in ZnO thin-film transistors using device simulation. <i>Applied Physics Letters</i> , <b>2010</b> , 97, 163503	3.4	12
74	Analysis of Hump Characteristics in Thin-Film Transistors With ZnO Channels Deposited by Sputtering at Various Oxygen Partial Pressures. <i>IEEE Electron Device Letters</i> , <b>2010</b> ,	4.4	25
73	69.1: Photo-Leakage Current in ZnO TFTs for Transparent Electronics. <i>Digest of Technical Papers SID International Symposium</i> , <b>2010</b> , 41, 1029	0.5	4
72	Growth characteristics of single-crystalline ZnMgO layers by ultrasonic spray assisted mist CVD technique. <i>Physica Status Solidi (B): Basic Research</i> , <b>2010</b> , 247, 1460-1463	1.3	28
71	Corundum-structured $\beta$ -phase Ga <sub>2</sub> O <sub>3</sub> -Cr <sub>2</sub> O <sub>3</sub> -Fe <sub>2</sub> O <sub>3</sub> alloy system for novel functions. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2010</b> , 7, 2467-2470		27
70	Flame Detection by a $\beta$ -Ga <sub>2</sub> O <sub>3</sub> -Based Sensor. <i>Japanese Journal of Applied Physics</i> , <b>2009</b> , 48, 011605	1.4	111
69	$\beta$ -Al <sub>2</sub> xGa <sub>2-2x</sub> O <sub>3</sub> Thin Film Growth by Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>2009</b> , 48, 070202	1.4	91
68	Epitaxial ZnO Thin Films on a-Plane Sapphire Substrates Grown by Ultrasonic Spray-Assisted Mist Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2009</b> , 48, 121103	1.4	41
67	Fabrication of Highly Crystalline Corundum-Structured $\beta$ -(Ga <sub>1-x</sub> Fe <sub>x</sub> ) <sub>2</sub> O <sub>3</sub> Alloy Thin Films on Sapphire Substrates. <i>Applied Physics Express</i> , <b>2009</b> , 2, 075501	2.4	69

66	Mist deposition technique as a green chemical route for synthesizing oxide and organic thin films. <i>Materials Research Society Symposia Proceedings</i> , <b>2009</b> , 1220, 4061		3
65	Heteroepitaxy of Corundum-Structured $\text{Ga}_2\text{O}_3$ Thin Films on $\text{Al}_2\text{O}_3$ Substrates by Ultrasonic Mist Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 7311-7313	1.4	295
64	Growth of Crystalline Zinc Oxide Thin Films by Fine-Channel-Mist Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2008</b> , 47, 4669-4675	1.4	89
63	Vertical Solar-Blind Deep-Ultraviolet Schottky Photodetectors Based on $\text{Ga}_2\text{O}_3$ Substrates. <i>Applied Physics Express</i> , <b>2008</b> , 1, 011202	2.4	270
62	Ultrasonic spray assisted Mist-CVD method for high-quality crystalline and amorphous oxide semiconductors growth. <i>Materials Research Society Symposia Proceedings</i> , <b>2008</b> , 1113, 1		
61	Properties of $\text{Ga}_2\text{O}_3$ -based $(\text{In}_x\text{Ga}_{1-x})_2\text{O}_3$ alloy thin films grown by molecular beam epitaxy. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 3113-3115		60
60	An approach for single crystalline zinc oxide thin films with fine channel mist chemical vapor deposition method. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2008</b> , 5, 3138-3140		27
59	Step-flow growth of homoepitaxial ZnO thin films by ultrasonic spray-assisted MOVPE. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 5007-5010	1.6	22
58	Surface morphology of homoepitaxial $\text{Ga}_2\text{O}_3$ thin films grown by molecular beam epitaxy. <i>Thin Solid Films</i> , <b>2008</b> , 516, 5768-5771	2.2	112
57	$\text{Ga}_2\text{O}_3$ Thin Film Growth on Plane Sapphire Substrates by Molecular Beam Epitaxy for Deep-Ultraviolet Photodetectors. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, 7217-7220	1.4	399
56	Low-Temperature Growth of ZnO Thin Films by Linear Source Ultrasonic Spray Chemical Vapor Deposition. <i>Japanese Journal of Applied Physics</i> , <b>2007</b> , 46, 6811-6813	1.4	60
55	Direct Fabrication of ZnO Whiskers Bridging Between Micron-gap Electrodes in Aqueous Solution for Highly Gas Sensing. <i>Materials Research Society Symposia Proceedings</i> , <b>2007</b> , 1035, 1		
54	Linear-Source Ultrasonic Spray Chemical Vapor Deposition Method for Fabrication of ZnMgO Films and Ultraviolet Photodetectors. <i>Japanese Journal of Applied Physics</i> , <b>2006</b> , 45, L857-L859	1.4	77
53	Fabrication and Properties of ZnO Thin Films Prepared by Fine Channel Mist Method. <i>Zairyo/Journal of the Society of Materials Science, Japan</i> , <b>2006</b> , 55, 153-158	0.1	27
52	Fabrication of wide-band-gap $\text{Mg}_x\text{Zn}_{1-x}\text{O}$ quasi-ternary alloys by molecular-beam epitaxy. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 192911	3.4	85
51	Molecular Beam Epitaxy of High Magnesium Content Single-Phase Wurzite $\text{Mg}_x\text{Zn}_{1-x}\text{O}$ Alloys ( $x \leq 0.5$ ) and Their Application to Solar-Blind Region Photodetectors. <i>Japanese Journal of Applied Physics</i> , <b>2003</b> , 42, L401-L403	1.4	152
50	Selective formation of ZnO nanodots on nanopatterned substrates by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2003</b> , 83, 3593-3595	3.4	35
49	Self-organized ZnO quantum dots on $\text{SiO}_2/\text{Si}$ substrates by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , <b>2002</b> , 81, 5036-5038	3.4	135

48	Hexagonal GaN grown on GaAs{11n} substrates by metalorganic vapor-phase epitaxy using AlAs intermediate layers. <i>Applied Physics Letters</i> , <b>2001</b> , 79, 4133-4135	3.4	6
47	Vacuum Deposition and Luminescence Dynamics of Organic Thin Film Multi-Structures. <i>Shinku/Journal of the Vacuum Society of Japan</i> , <b>2001</b> , 44, 948-955		
46	Single-phase hexagonal GaN grown on AlAs/GaAs(001). <i>Applied Physics Letters</i> , <b>2000</b> , 77, 244-246	3.4	7
45	Six-bilayer periodic structures in GaN grown on GaAs(001). <i>Applied Physics Letters</i> , <b>2000</b> , 76, 330-332	3.4	3
44	Integration of GaN with Si using a AuGe-mediated wafer bonding technique. <i>Applied Physics Letters</i> , <b>2000</b> , 77, 3959-3961	3.4	14
43	Electrical Characterization of MOVPE-Grown P-Type GaN:Mg Against Annealing Temperature. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , <b>1999</b> , 4, 665-670		1
42	Tunable band offsets via control of interface atomic configuration in GaAs-on-ZnSe(001) heterovalent heterostructures. <i>Journal of Applied Physics</i> , <b>1999</b> , 85, 1514-1519	2.5	5
41	Relation between GaAs surface morphology and incorporation of hexagonal GaN into cubic GaN. <i>Journal of Crystal Growth</i> , <b>1999</b> , 196, 41-46	1.6	18
40	Luminescence Dynamics of Alq3-Based Multilayer Structures in Terms of HOMO and LUMO Energy Discontinuity. <i>Materials Research Society Symposia Proceedings</i> , <b>1999</b> , 598, 321		
39	Growth of p-type Zn(S)Se layers by MOVPE. <i>Journal of Crystal Growth</i> , <b>1998</b> , 184-185, 398-405	1.6	10
38	A comparative study on deep levels in p-ZnSe grown by MBE, MOMBE and MOVPE. <i>Journal of Crystal Growth</i> , <b>1998</b> , 184-185, 495-499	1.6	2
37	The mechanism of radiative recombination in light-emitting devices composed on InGaN quantum wells. <i>Electronics and Communications in Japan</i> , <b>1998</b> , 81, 45-56		2
36	Nucleation processes during metalorganic vapor phase epitaxy of ZnSe on GaAs(001). <i>Journal of Applied Physics</i> , <b>1998</b> , 84, 1383-1388	2.5	2
35	Deep states in nitrogen-doped p-ZnSe. <i>Journal of Applied Physics</i> , <b>1998</b> , 83, 2563-2567	2.5	5
34	Optical Absorption in ZnSe-GaAs Heterovalent Quantum Structures. <i>Materials Research Society Symposia Proceedings</i> , <b>1998</b> , 535, 71		
33	Electrical Characterization of Movpe-Grown p-Type GaN:Mg Against Annealing Temperature. <i>Materials Research Society Symposia Proceedings</i> , <b>1998</b> , 537, 1		2
32	Stimulated emission from optically pumped GaN quantum dots. <i>Applied Physics Letters</i> , <b>1997</b> , 71, 1299-1301	3.4	74
31	Tunable band offsets in ZnSe/GaAs heterovalent heterostructures grown by metalorganic vapor phase epitaxy. <i>Journal of Applied Physics</i> , <b>1997</b> , 82, 2984-2989	2.5	13

30	Self-organized CdSe quantum dots onto cleaved GaAs (110) originating from Stranski-Krastanow growth mode. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 3278-3280	3-4	54
29	Role of self-formed InGaN quantum dots for exciton localization in the purple laser diode emitting at 420 nm. <i>Applied Physics Letters</i> , <b>1997</b> , 70, 981-983	3-4	835
28	Effect of cleaving environment on the growth of ZnSe on the GaAs (1 1 0) surface by molecular beam epitaxy. <i>Journal of Materials Science Letters</i> , <b>1997</b> , 16, 1187-1190		
27	Effect of cleaving environment on the growth of ZnSe on the GaAs (110) surface by molecular beam epitaxy. <i>Journal of Materials Science Letters</i> , <b>1997</b> , 16, 1187-1190		
26	Molecular Beam Epitaxial Growth Behaviors of Zn <sub>1-x</sub> Cd <sub>x</sub> Se on the GaAs(110) Surface Cleaved in Ultra High Vacuum.. <i>Shinku/Journal of the Vacuum Society of Japan</i> , <b>1997</b> , 40, 317-320		
25	Defect States in p-ZnSe:N Grown by MOVPE. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 442, 561		
24	Surface Reconstruction and Morphology of Hydrogen Sulfide Treated GaAs (001) Substrate. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 448, 15		
23	Emission Mechanism of the InGaN MQW Grown by MOCVD. <i>Materials Research Society Symposia Proceedings</i> , <b>1996</b> , 449, 665		
22	Effects of GaAs buffer layer and lattice-matching on deep levels in Zn(S)Se/GaAs heterostructures. <i>Journal of Electronic Materials</i> , <b>1996</b> , 25, 217-222	1.9	5
21	Growth of P-type Znse by metalorganic molecular beam epitaxy using metal Zn and dimethylselenide. <i>Journal of Electronic Materials</i> , <b>1996</b> , 25, 223-227	1.9	4
20	Effects of annealing atmosphere and temperature on acceptor activation in ZnSe:N grown by photoassisted MOVPE. <i>Journal of Crystal Growth</i> , <b>1996</b> , 159, 312-316	1.6	46
19	MO(GS)MBE and photo-MO(GS)MBE of II <sup>VI</sup> semiconductors. <i>Journal of Crystal Growth</i> , <b>1996</b> , 164, 196-201.6	1.6	10
18	Photoassisted growth of II <sup>VI</sup> semiconductor films. <i>Applied Surface Science</i> , <b>1995</b> , 86, 431-436	6.7	11
17	Growth of ZnSe/ZnMgSSe quantum well structures by metalorganic molecular beam epitaxy under in situ observation of reflection high energy electron diffraction intensity oscillation. <i>Journal of Crystal Growth</i> , <b>1995</b> , 150, 738-742	1.6	3
16	Thermal annealing effects on p-type conductivity of nitrogendoped ZnSe grown by metalorganic vapor phase epitaxy. <i>Journal of Electronic Materials</i> , <b>1995</b> , 24, 137-141	1.9	15
15	Gas-Source Molecular Beam Epitaxial Growth of (Zn, Mg)(S, Se) Using Bis-methylcyclopentadienyl-magnesium and Hydrogen Sulfide. <i>Japanese Journal of Applied Physics</i> , <b>1994</b> , 33, L290-L293	1.4	16
14	Photocatalytic surface reactions in metalorganic vapor-phase epitaxy. <i>Applied Surface Science</i> , <b>1994</b> , 79-80, 41-46	6.7	7
13	Photo-assisted metalorganic vapor-phase epitaxy for nitrogen doping and fabrication of blue-green light emitting devices of ZnSe-based semiconductors. <i>Journal of Crystal Growth</i> , <b>1994</b> , 138, 737-744	1.6	15



12	Metalorganic vapor-phase epitaxy of p-type ZnSe and p/n junction diodes. <i>Journal of Crystal Growth</i> , <b>1994</b> , 145, 552-556	1.6	15
11	Metalorganic vapor phase epitaxy growth and nitrogen-doping of Zn <sub>x</sub> Cd <sub>1-x</sub> S using photo-assistance. <i>Journal of Crystal Growth</i> , <b>1994</b> , 145, 570-575	1.6	5
10	Photoassisted Metalorganic Vapor-Phase Epitaxy of Nitrogen-Doped ZnSe Using Tertiarybutylamine as Doping Source. <i>Japanese Journal of Applied Physics</i> , <b>1993</b> , 32, L1153-L1156	1.4	21
9	Fabrication of II-VI semiconductor quantum well structures in ZnCdSSe alloy systems. <i>Physica B: Condensed Matter</i> , <b>1993</b> , 191, 57-70	2.8	9
8	Optically Pumped Blue-Green Laser Operation Above Room-Temperature in Zn <sub>0.80</sub> Cd <sub>0.20</sub> Se-Zn <sub>0.08</sub> Se <sub>0.92</sub> Multiple Quantum Well Structures Grown by Metalorganic Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , <b>1991</b> , 30, L605-L607	1.4	43
7	A Defect Model for Photoirradiated Semiconductors – Suppression of the Self-Compensation in II-VI Materials – <i>Japanese Journal of Applied Physics</i> , <b>1991</b> , 30, 3475-3481	1.4	31
6	Organometallic vapor-phase epitaxial growth of cubic ZnCdS lattice-matched to GaAs substrate. <i>Journal of Crystal Growth</i> , <b>1990</b> , 99, 437-440	1.6	22
5	Metalorganic Molecular Beam Epitaxial Growth of ZnSe and ZnS on GaAs Substrates Pretreated with (NH <sub>4</sub> ) <sub>2</sub> S <sub>x</sub> Solution. <i>Japanese Journal of Applied Physics</i> , <b>1990</b> , 29, L144-L147	1.4	50
4	Rheed and x-ray characterization of InGaAs/GaAs grown by MBE. <i>Journal of Crystal Growth</i> , <b>1989</b> , 95, 224-227	1.6	36
3	Growth Rate Enhancement by Xenon Lamp Irradiation in Organometallic Vapor-Phase Epitaxy of ZnSe. <i>Japanese Journal of Applied Physics</i> , <b>1987</b> , 26, L2000-L2002	1.4	67
2	Mist Chemical Vapor Deposition Growth of In <sub>2</sub> O <sub>3</sub> Films Using Indium Oxide Powder as Source Precursor. <i>Physica Status Solidi (B): Basic Research</i> , 2100414	1.3	0
1	Vacuum Ultraviolet Emission Properties of Rocksalt-Structured MgZnO Microcrystals Prepared on Quartz Glass Substrates. <i>Physica Status Solidi (B): Basic Research</i> , 2100354	1.3	